NXP USA Inc. - FS32K144HFT0VLHT Datasheet

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, FlexIO, I²C, LINbus, SPI, UART/USART
Peripherals	POR, PWM, WDT
Number of I/O	58
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 16x12b SAR; D/A1x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/fs32k144hft0vlht

- Communications interfaces
  - Up to three Low Power Universal Asynchronous Receiver/Transmitter (LPUART/LIN) modules with DMA support and low power availability
  - Up to three Low Power Serial Peripheral Interface (LPSPI) modules with DMA support and low power availability
  - Up to two Low Power Inter-Integrated Circuit (LPI2C) modules with DMA support and low power availability
  - Up to three FlexCAN modules (with optional CAN-FD support)
  - FlexIO module for emulation of communication protocols and peripherals (UART, I2C, SPI, I2S, LIN, PWM, etc).
  - Up to one 10/100Mbps Ethernet with IEEE1588 support and two Synchronous Audio Interface (SAI) modules.
- Safety and Security
  - Cryptographic Services Engine (CSEc) implements a comprehensive set of cryptographic functions as described in the SHE (Secure Hardware Extension) Functional Specification. Note: CSEc (Security) or EEPROM writes/erase will trigger error flags in HSRUN mode (112 MHz) because this use case is not allowed to execute simultaneously. The device will need to switch to RUN mode (80 MHz) to execute CSEc (Security) or EEPROM writes/erase.
  - 128-bit Unique Identification (ID) number
  - Error-Correcting Code (ECC) on flash and SRAM memories
  - System Memory Protection Unit (System MPU)
  - Cyclic Redundancy Check (CRC) module
  - Internal watchdog (WDOG)
  - External Watchdog monitor (EWM) module
- Timing and control
  - Up to eight independent 16-bit FlexTimers (FTM) modules, offering up to 64 standard channels (IC/OC/PWM)
  - One 16-bit Low Power Timer (LPTMR) with flexible wake up control
  - Two Programmable Delay Blocks (PDB) with flexible trigger system
  - One 32-bit Low Power Interrupt Timer (LPIT) with 4 channels
  - 32-bit Real Time Counter (RTC)
- Package
  - 32-pin QFN, 48-pin LQFP, 64-pin LQFP, 100-pin LQFP, 100-pin MAPBGA, 144-pin LQFP, 176-pin LQFP package options
- 16 channel DMA with up to 63 request sources using DMAMUX

3 Ordering information

3.1 Selecting orderable part number

Not all part number combinations are available. See the attachment *S32K1xx_Orderable_Part_Number_ List.xlsx* attached with the Datasheet for a list of standard orderable part numbers.

4. When input pad voltage levels are close to V_{DD} or V_{SS}, practically no current injection is possible.
5. While respecting the maximum current injection limit
6. This is the Electronic Control Unit (ECU) supply ramp rate and not directly the MCU ramp rate. Limit applies to both maximum absolute maximum ramp rate and typical operating conditions.
7. This is the MCU supply ramp rate and the ramp rate assumes that the S32K1xx HW design guidelines in AN5426 are followed. Limit applies to both maximum absolute maximum ramp rate and typical operating conditions.
8. T_J (Junction temperature)=135 °C. Assumes T_A=125 °C for RUN mode

   T_J (Junction temperature)=125 °C. Assumes TA=105 °C for HSRUN mode

   - Assumes maximum θJA for 2s2p board. See Thermal characteristics
9. 60 seconds lifetime; device in reset (no outputs enabled/toggling)

4.2 Voltage and current operating requirements

NOTE

Device functionality is guaranteed up to the LVR assert level, however electrical performance of 12-bit ADC, CMP with 8-bit DAC, IO electrical characteristics, and communication modules electrical characteristics would be degraded when voltage drops below 2.7 V

Table 2. Voltage and current operating requirements [1]

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}[2]	Supply voltage	2.7[3]	5.5	V	4
V_{DD_OFF}	Voltage allowed to be developed on V_{DD} pin when it is not powered from any external power supply source.	0	0.1	V	
V_{DDA}	Analog supply voltage	2.7	5.5	V	4
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	– 0.1	0.1	V	4
V_{REFH}	ADC reference voltage high	2.7	V_{DDA} + 0.1	V	5
V_{REFL}	ADC reference voltage low	-0.1	0.1	V	
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	6
$I_{INJPAD\_DC\_OP}$[7]	Continuous DC input current (positive / negative) that can be injected into an I/O pin	-3	+3	mA	
$I_{INJSUM\_DC\_OP}$	Continuous total DC input current that can be injected across all I/O pins such that there's no degradation in accuracy of analog modules: ADC and ACMP (See section Analog Modules)	—	30	mA	

1. Typical conditions assumes $V_{DD} = V_{DDA} = V_{REFH}$ = 5 V, temperature = 25 °C and typical silicon process unless otherwise stated.
2. As V_{DD} varies between the minimum value and the absolute maximum value the analog characteristics of the I/O and the ADC will both change. See section I/O parameters and ADC electrical specifications respectively for details.
3. S32K148 will operate from 2.7 V when executing from internal FIRC. When the PLL is engaged S32K148 is guaranteed to operate from 2.97 V. All other S32K family devices operate from 2.7 V in all modes.
4. V_{DD} and V_{DDA} must be shorted to a common source on PCB. The differential voltage between V_{DD} and V_{DDA} is for RF-AC only. Appropriate decoupling capacitors to be used to filter noise on the supplies. See application note AN5032 for reference supply design for SAR ADC.

Table 7. Power consumption (Typicals unless stated otherwise) [1] (continued)

Chip/Device	Ambient Temperature (°C)		VLPS (µA) [2]		VLPR (mA)			STOP1 (mA)	STOP2 (mA)	RUN@48 MHz (mA)		RUN@64 MHz (mA)		RUN@80 MHz (mA)		HSRUN@112 MHz (mA) [3]		IDD/MHz (µA/MHz) [4]
			Peripherals disabled [5]	Peripherals enabled	Peripherals disabled [6]	Peripherals enabled use case 1 [6]	Peripherals enabled use case 2 [7]			Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	
		Max	1637	1694	3.1	3.21	NA	12.7	13.7	25	32.9	30.7	38.8	36	43.8	NA		450
S32K144	25	Typ	29.8	42	1.48	1.50	2.91	7	7.7	19.7	26.9	25.1	33.3	30.2	39.6	43.3	55.6	378
	85	Typ	150	159	1.72	1.85	3.08	7.2	8.1	20.4	27.1	26.1	33.5	30.5	40	43.9	56.1	381
		Max	359	384	2.60	2.65	NA	9.2	9.9	23.2	29.6	29.3	36.2	34.8	42.1	46.3	59.7	435
	105	Typ	256	273	1.80	2.10	3.23	7.8	8.5	20.6	27.4	26.6	33.8	31.2	40.5	44.8	57.1	390
		Max	850	900	2.65	2.70	NA	10.3	11.1	23.9	30.6	30.3	37.3	35.6	43.5	47.9	61.3	445
	125	Typ	NA	NA	NA	NA	3.65	NA	NA	NA	NA	NA	NA	NA	NA	NA		NA
		Max	1960	1998	3.18	3.25	NA	12.9	13.8	26.9	33.6	35	40.3	38.7	46.8	NA		484
S32K146	25	Typ	37	47	1.57	1.61	3.3	8	9.2	23.4	31.4	30.5	40.2	36.2	47.6	52	68.3	452
	85	Typ	207	209	1.79	1.83	3.54	8.9	10.1	24.4	32.4	31.5	41.3	37.2	48.7	53.3	69.8	465
		Max	974	981	3.32	3.38	NA	12.7	13.9	29.3	37.9	36.7	47	42.4	54.4	60.3	78	530
	105	Typ	419	422	1.99	2.04	3.78	9.8	11	25.3	33.4	32.5	42.2	38.1	49.6	54.4	70.8	477
		Max	2004	2017	4.06	4.13	NA	17.1	18.3	34.1	42.6	41.3	51.4	46.9	58.8	65.7	82.8	587
	125	Typ	NA	NA	NA	NA	4.44	NA	NA	NA	NA	NA	NA	NA	NA	NA		NA
		Max	3358	3380	5.28	5.38	NA	22.6	23.7	40.2	48.8	47.3	57.4	52.8	64.8	NA		660
S32K148[8]	25	Typ	38	54	2.17	2.20	3.45	8.5	9.6	27.6	34.9	35.5	45.3	42.1	57.7	60.3	83.3	526
	85	Typ	336	357	2.30	2.35	3.74	10.1	11.1	29.1	37.0	36.8	46.6	43.4	59.9	62.9	88.7	543

Table continues on the next page...

Table 7. Power consumption (Typicals unless stated otherwise) [1] (continued)

Chip/Device	Ambient Temperature (°C)		VLPS (µA) [2]		VLPR (mA)			STOP1 (mA)	STOP2 (mA)	RUN@48 MHz (mA)		RUN@64 MHz (mA)		RUN@80 MHz (mA)		HSRUN@112 MHz (mA) [3]		IDD/MHz (µA/MHz) [4]
			Peripherals disabled [5]	Peripherals enabled	Peripherals disabled [6]	Peripherals enabled use case 1 [6]	Peripherals enabled use case 2 [7]			Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	
		Max	1660	1736	3.48	3.55	NA	14.5	15.6	34.8	43.6	41.9	53.9	48.7	65.1	70.4	96.1	609
	105	Typ	560	577	2.49	2.54	4.03	10.9	11.9	29.8	37.8	37.6	47.5	45.2	61.5	63.8	89.1	565
		Max	2945	2970	4.40	4.47	NA	18.0	19.0	38.4	46.8	44.9	55.3	51.6	66.8	73.6	97.4	645
	125	Typ	NA	NA	NA	NA	4.85	NA	NA	NA	NA	NA	NA	NA	NA	NA		NA
		Max	3990	4166	6.00	6.08	NA	23.4	24.5	44.3	52.5	50.9	61.3	57.5	71.6	NA		719

1. Typical current numbers are indicative for typical silicon process and may vary based on the silicon distribution and user configuration. Typical conditions assumes $V_{DD} = V_{DDA} = V_{REFH} = 5$ V, temperature = 25 °C and typical silicon process unless otherwise stated. All output pins are floating and On-chip pulldown is enabled for all unused input pins.
2. Current numbers are for reduced configuration and may vary based on user configuration and silicon process variation.
3. HSRUN mode must not be used at 125°C. Max ambient temperature for HSRUN mode is 105°C.
4. Values mentioned for S32K14x devices are measured at RUN@80 MHz with peripherals disabled and values mentioned for S32K11x devices are measured at RUN@48 MHz with peripherals disabled.
5. With PMC_REGSC[CLKBIASDIS] set to 1. See Reference Manual for details.
6. Data collected using RAM
7. Numbers on limited samples size and data collected with Flash
8. The S32K148 data points assume that ENET/QuadSPI/SAI etc. are inactive.

5.3 DC electrical specifications at 3.3 V Range

NOTE

For details on the pad types defined in Table 11 and Table 12, see Reference Manual section *IO Signal Table* and IO Signal Description Input Multiplexing sheet(s) attached with Reference Manual.

Table 11. DC electrical specifications at 3.3 V Range

Symbol	Parameter	Value			Unit	Notes
		Min.	Typ.	Max.		
V_{DD}	I/O Supply Voltage	2.7	3.3	4	V	1
V_{ih}	Input Buffer High Voltage	0.7 × V_{DD}	—	V_{DD} + 0.3	V	2
V_{il}	Input Buffer Low Voltage	V_{SS} – 0.3	—	0.3 × V_{DD}	V	3
V_{hys}	Input Buffer Hysteresis	0.06 × V_{DD}	—	—	V	
Ioh_{GPIO} $Ioh_{GPIO\text{-}HD\_DSE\_0}$	I/O current source capability measured when pad V_{oh} = (V_{DD} – 0.8 V)	3.5	—	—	mA	
Iol_{GPIO} $Iol_{GPIO\text{-}HD\_DSE\_0}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	3	—	—	mA	
$Ioh_{GPIO\text{-}HD\_DSE\_1}$	I/O current source capability measured when pad V_{oh} = (V_{DD} – 0.8 V)	14	—	—	mA	4
$Iol_{GPIO\text{-}HD\_DSE\_1}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	12	—	—	mA	4
$Ioh_{GPIO\text{-}FAST\_DSE\_0}$	I/O current sink capability measured when pad V_{oh}=V_{DD}-0.8 V	9.5	—	—	mA	5
$Iol_{GPIO\text{-}FAST\_DSE\_0}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	10	—	—	mA	5
$Ioh_{GPIO\text{-}FAST\_DSE\_1}$	I/O current sink capability measured when pad V_{oh}=V_{DD}-0.8 V	16	—	—	mA	5
$Iol_{GPIO\text{-}FAST\_DSE\_1}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	15.5	—	—	mA	5
IOHT	Output high current total for all ports	—	—	100	mA	
IIN	Input leakage current (per pin) for full temperature range at V_{DD} = 3.3 V					6
	All pins other than high drive port pins		0.005	0.5	μA	
	High drive port pins [7]		0.010	0.5	μA	
R_{PU}	Internal pullup resistors	20		60	kΩ	8
R_{PD}	Internal pulldown resistors	20		60	kΩ	9

1. S32K148 will operate from 2.7 V when executing from internal FIRC. When the PLL is engaged S32K148 is guaranteed to operate from 2.97 V. All other S32K family devices operate from 2.7 V in all modes.
2. For reset pads, same V_{ih} levels are applicable
3. For reset pads, same V_{il} levels are applicable
4. The value given is measured at high drive strength mode. For value at low drive strength mode see the Ioh_Standard value given above.
5. For refernce only. Run simulations with the IBIS model and custom board for accurate results.

Table 14. AC electrical specifications at 5 V Range (continued)

Symbol	DSE	Rise time (nS)[1]		Fall time (nS) [1]		Capacitance (pF) [2]
		Min.	Max .	Min.	Max.	
		17.3	54.8	17.6	59.7	200
	1	1.1	4.6	1.1	5.0	25
		2.0	5.7	2.0	5.8	50
		5.4	16.0	5.0	16.0	200
$tRF_{GPIO-FAST}$	0	0.42	2.2	0.37	2.2	25
		2.0	5.0	1.9	5.2	50
		9.3	18.8	8.5	19.3	200
	1	0.37	0.9	0.35	0.9	25
		1.2	2.7	1.2	2.9	50
		6.0	11.8	6.0	12.3	200

1. For reference only. Run simulations with the IBIS model and your custom board for accurate results.
2. Maximum capacitances supported on Standard IOs. However interface or protocol specific specifications might be different, for example for ENET, QSPI etc. . For protocol specific AC specifications, see respective sections.

5.7 Standard input pin capacitance

Table 15. Standard input pin capacitance

Symbol	Description	Min.	Max.	Unit
C_{IN_D}	Input capacitance: digital pins	—	7	pF

NOTE

Please refer to External System Oscillator electrical specifications for EXTAL/XTAL pins.

5.8 Device clock specifications

Table 16. Device clock specifications [1]

Symbol	Description	Min.	Max.	Unit
High Speed run mode[2]				
f_{SYS}	System and core clock	—	112	MHz
f_{BUS}	Bus clock	—	56	MHz
f_{FLASH}	Flash clock	—	28	MHz
Normal run mode (S32K11x series)				
f_{SYS}	System and core clock	—	48	MHz
f_{BUS}	Bus clock	—	48	MHz

Table continues on the next page...

Table 18. External System Oscillator frequency specifications

Symbol	Description	Min.		Typ.		Max.		Unit	Notes
		S32K14x	S32K11x	S32K14x	S32K11x	S32K14x	S32K11x		
f_{osc_hi}	Oscillator crystal or resonator frequency	4		—		40		MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—		—		50	48	MHz	1
t_{dc_extal}	Input clock duty cycle (external clock mode)	48		50		52		%	1
t_{cst}	Crystal Start-up Time								
	8 MHz low-gain mode (HGO=0)	—		1.5		—		ms	2
	8 MHz high-gain mode (HGO=1)	—		2.5		—			
	40 MHz low-gain mode (HGO=0)	—		2		—			
	40 MHz high-gain mode (HGO=1)	—		2		—			

1. Frequencies below 40 MHz can be used for degraded duty cycle upto 40-60%
2. Proper PC board layout procedures must be followed to achieve specifications.

6.2.3 System Clock Generation (SCG) specifications

6.2.3.1 Fast internal RC Oscillator (FIRC) electrical specifications

Table 19. Fast internal RC Oscillator electrical specifications

Symbol	Parameter[1]	Value			Unit
		Min.	Typ.	Max.	
F_{FIRC}	FIRC target frequency	—	48	—	MHz
ΔF	Frequency deviation across process, voltage, and temperature < 105°C	—	±0.5	±1	$\%F_{FIRC}$
ΔF125	Frequency deviation across process, voltage, and temperature < 125°C	—	±0.5	±1.1	$\%F_{FIRC}$
$T_{Startup}$	Startup time		3.4	5	μs[2]
T_{JIT},[3]	Cycle-to-Cycle jitter	—	300	500	ps
T_{JIT}[3]	Long term jitter over 1000 cycles	—	0.04	0.1	$\%F_{FIRC}$

1. With FIRC regulator enable
2. Startup time is defined as the time between clock enablement and clock availability for system use.
3. FIRC as system clock

NOTE

Fast internal RC Oscillator is compliant with CAN and LIN standards.

6.2.3.2 Slow internal RC oscillator (SIRC) electrical specifications

Table 20. Slow internal RC oscillator (SIRC) electrical specifications

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
F_{SIRC}	SIRC target frequency	—	8	—	MHz
ΔF	Frequency deviation across process, voltage, and temperature < 105°C	—	—	±3	$\%F_{SIRC}$
ΔF125	Frequency deviation across process, voltage, and temperature < 125°C	—	—	±3.3	$\%F_{SIRC}$
$T_{Startup}$	Startup time	—	9	12.5	μs[1]

1. Startup time is defined as the time between clock enablement and clock availability for system use.

6.2.4 Low Power Oscillator (LPO) electrical specifications

Table 21. Low Power Oscillator (LPO) electrical specifications

Symbol	Parameter	Min.	Typ.	Max.	Unit
F_{LPO}	Internal low power oscillator frequency	113	128	139	kHz
$T_{startup}$	Startup Time	—	—	20	μs

6.2.5 SPLL electrical specifications

Table 22. SPLL electrical specifications

Symbol	Parameter	Min.	Typ.	Max.	Unit
F_{SPLL_REF}[1]	PLL Reference Frequency Range	8	—	16	MHz
F_{SPLL_Input}[2]	PLL Input Frequency	8	—	40	MHz
F_{VCO_CLK}	VCO output frequency	180	—	320	MHz
F_{SPLL_CLK}	PLL output frequency	90	—	160	MHz
J_{CYC_SPLL}	PLL Period Jitter (RMS)[3]				
	at F_{VCO_CLK} 180 MHz	—	120	—	ps
	at F_{VCO_CLK} 320 MHz	—	75	—	ps
J_{ACC_SPLL}	PLL accumulated jitter over 1μs (RMS)[3]				
	at F_{VCO_CLK} 180 MHz	—	1350	—	ps
	at F_{VCO_CLK} 320 MHz	—	600	—	ps
D_{UNL}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%
T_{SPLL_LOCK}	Lock detector detection time[4]	—	—	$150 \times 10^{-6} + 1075(1/F_{SPLL\_REF})$	s

1. F_{SPLL_REF} is PLL reference frequency range after the PREDIV. For PREDIV and MULT settings refer SCG_SPLLCFG register of Reference Manual.
2. F_{SPLL_Input} is PLL input frequency range before the PREDIV must be limited to the range 8 MHz to 40 MHz. This input source could be derived from a crystal oscillator or some other external square wave clock source using OSC bypass mode. For external clock source settings refer SCG_SOSCCFG register of Reference Manual.
3. This specification was obtained using a NXP developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary
4. Lock detector detection time is defined as the time between PLL enablement and clock availability for system use.

6.3 Memory and memory interfaces

6.3.1 Flash memory module (FTFC) electrical specifications

This section describes the electrical characteristics of the flash memory module.

Table 24. Flash command timing specifications for S32K11x (continued)

Symbol	Description[1]		S32K116		S32K118			
			Typ	Max	Typ	Max	Unit	Notes
t_{ersscr}	Erase Flash Sector execution time	—	12	130	12	130	ms	2
$t_{pgmsec1k}$	Program Section execution time (1 KB flash)	—	5	—	5	—	ms	
t_{rd1all}	Read 1s All Block execution time	—	—	1.7	—	2.8	ms	
t_{rdonce}	Read Once execution time	—	—	30	—	30	μs	
$t_{pgmonce}$	Program Once execution time	—	90	—	90	—	μs	
t_{ersall}	Erase All Blocks execution time	—	150	1500	230	2500	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	35	—	35	μs	
$t_{ersallu}$	Erase All Blocks Unsecure execution time	—	150	1500	230	2500	ms	2
$t_{pgmpart}$	Program Partition for EEPROM execution time	32 KB EEPROM backup	71	—	71	—	ms	3
		64 KB EEPROM backup	—	—	—	—		
t_{setram}	Set FlexRAM Function execution time	Control Code 0xFF	0.08	—	0.08	—	ms	3
		32 KB EEPROM backup	0.8	1.2	0.8	1.2		
		48 KB EEPROM backup	—	—	—	—		
		64 KB EEPROM backup	—	—	—	—		
t_{eewr8b}	Byte write to FlexRAM execution time	32 KB EEPROM backup	385	1700	385	1700	μs	3,4
		48 KB EEPROM backup	—	—	—	—		
		64 KB EEPROM backup	—	—	—	—		
$t_{eewr16b}$	16-bit write to FlexRAM execution time	32 KB EEPROM backup	385	1700	385	1700	μs	3,4
		48 KB EEPROM backup	—	—	—	—		
		64 KB EEPROM backup	—	—	—	—		
$t_{eewr32bers}$	32-bit write to erased FlexRAM location execution time	—	360	2000	360	2000	μs	

Table continues on the next page...

Table 24. Flash command timing specifications for S32K11x (continued)

Symbol	Description[1]		S32K116		S32K118			
			Typ	Max	Typ	Max	Unit	Notes
$t_{eewr32b}$	32-bit write to FlexRAM execution time	32 KB EEPROM backup	630	2000	630	2000	μs	3, 4
		48 KB EEPROM backup	—	—	—	—		
		64 KB EEPROM backup	—	—	—	—		
$t_{quickwr}$	32-bit Quick Write execution time: Time from CCIF clearing (start the write) until CCIF setting (32-bit write complete, ready for next 32-bit write)	1st 32-bit write	200	550	200	550	μs	4, 5, 6
		2nd through Next to Last (Nth-1) 32-bit write	150	550	150	550		
		Last (Nth) 32-bit write (time for write only, not cleanup)	200	550	200	550		
$t_{quickwrClnup}$	Quick Write Cleanup execution time	—	—	(# of Quick Writes) * 2.0	—	(# of Quick Writes) * 2.0	ms	7

1. All command times assume 25 MHz or greater flash clock frequency (for synchronization time between internal/external clocks).
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For all EEPROM Emulation terms, the specified timing shown assumes previous record cleanup has occurred. This may be verified by executing FCCOB Command 0x77, and checking FCCOB number 5 contents show 0x00 - No EEPROM issues detected.
4. 1st time EERAM writes after a Reset or SETRAM may incur additional overhead for EEE cleanup, resulting in up to 2x the times shown.
5. Only after the Nth write completes will any data be valid. Emulated EEPROM record scheme cleanup overhead may occur after this point even after a brownout or reset. If power on reset occurs before the Nth write completes, the last valid record set will still be valid and the new records will be discarded.
6. Quick Write times may take up to 550 μs, as additional cleanup may occur when crossing sector boundaries.
7. Time for emulated EEPROM record scheme overhead cleanup. Automatically done after last (Nth) write completes, assuming still powered. Or via SETRAM cleanup execution command is requested at a later point.

NOTE

Under certain circumstances FlexMEM maximum times may be exceeded. In this case the user or application may wait, or assert reset to the FTFC macro to stop the operation.

6.3.1.2 Reliability specifications

Table 25. NVM reliability specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
When using as Program and Data Flash						
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	—	—	years	1
$n_{nvmcycp}$	Cycling endurance	1 K	—	—	cycles	2, 3

Table continues on the next page...

Table 26. QuadSPI electrical specifications

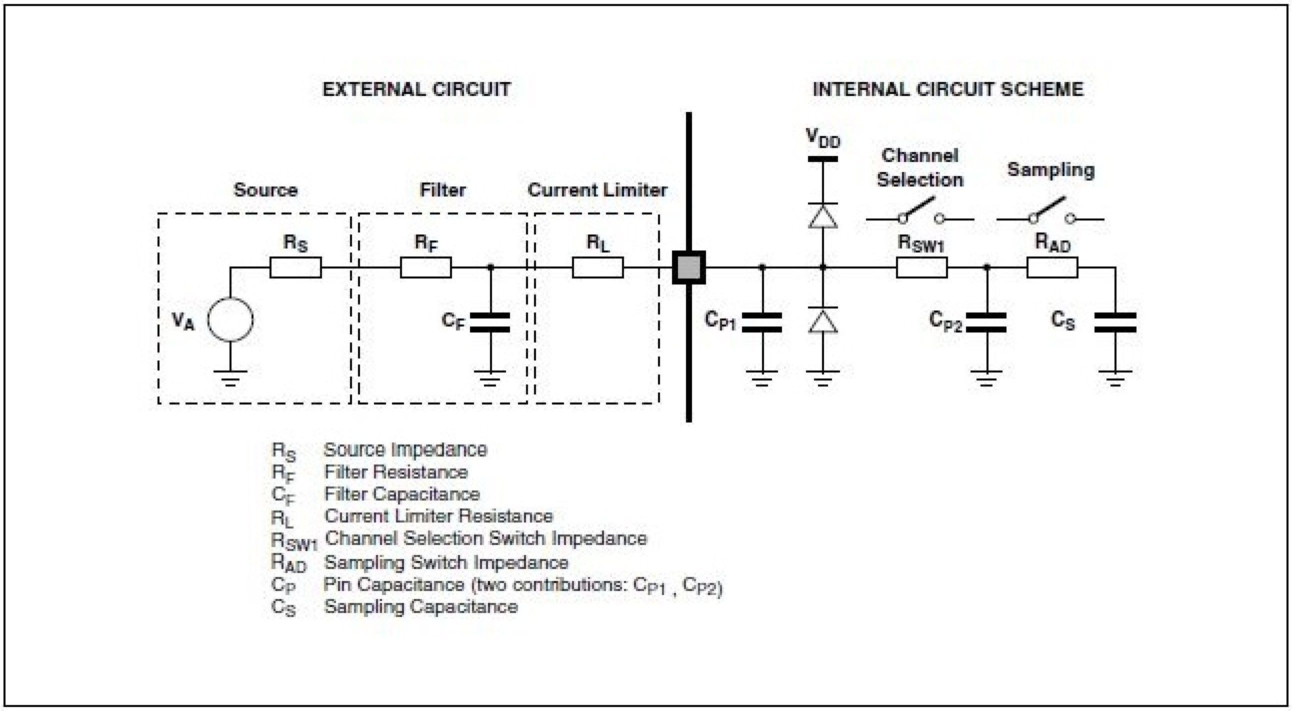
FLASH PORT	Sym	Unit	FLASH A												FLASH B			
			RUN[1]						HSRUN[1]						RUN/HSRUN[2]			
QuadSPI Mode			SDR						SDR						SDR		DDR[3]	
			Internal Sampling		Internal DQS				Internal Sampling		Internal DQS				Internal Sampling		External DQS	
			N1		PAD Loopback		Internal Loopback		N1		PAD Loopback		Internal Loopback		N1		External DQS	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
Register Settings																		
MCR[DDR_EN]		-	0		0		0		0		0		0		0		1	
MCR[DQS_EN]		-	0		1		1		0		1		1		0		1	
MCR[SCLKCFG[0]]		-	-		1		0		-		1		0		-		-	
MCR[SCLKCFG[1]]		-	-		1		0		-		1		0		-		-	
MCR[SCLKCFG[2]]		-	-		-		-		-		-		-		-		0	
MCR[SCLKCFG[3]]		-	-		-		-		-		-		-		-		0	
MCR[SCLKCFG[5]]		-	0		0		0		0		0		0		0		1	
SMPR[FSPHS]		-	0		1		0		0		1		0		0		0	
SMPR[FSDLY]		-	0		0		0		0		0		0		0		0	
SOCCR [SOCCFG[7:0]]			-		0		23		-		0		30		-		-	
SOCCR[SOCCFG[15:8]]		-	-		-		-		-		-		-		-		30	
FLSHCR[TDH]		-	0x00		0x00		0x00		0x00		0x00		0x00		0x00		0x01	
Timing Parameters																		
SCK Clock Frequency	f_{SCK}	MHz	-	38	-	64	-	48	-	40	-	80	-	50	-	20	-	20[4]
SCK Clock Period	t_{SCK}	ns	1/fSCK	-	1/fSCK	-	1/fSCK	-	1/fSCK	-	1/fSCK	-	1/fSCK	-	50.0	-	50.0[4]	-

Table continues on the next page...

Table 27. 12-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
f_{ADCK}	ADC conversion clock frequency	Normal usage	2	40	50	MHz	3, 4
f_{CONV}	ADC conversion frequency	No ADC hardware averaging.[5] Continuous conversions enabled, subsequent conversion time	46.4	928	1160	Ksps	6, 7
		ADC hardware averaging set to 32. [5] Continuous conversions enabled, subsequent conversion time	1.45	29	36.25	Ksps	6, 7

1. Typical values assume V_{DDA} = 5 V, Temp = 25 °C, f_{ADCK} = 40 MHz, R_{AS}=20 Ω, and C_{AS}=10 nF unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. For packages without dedicated V_{REFH} and V_{REFL} pins, V_{REFH} is internally tied to V_{DDA}, and V_{REFL} is internally tied to V_{SS}. To get maximum performance, reference supply quality should be better than SAR ADC. See application note AN5032 for details.
3. Clock and compare cycle need to be set according to the guidelines mentioned in the *Reference Manual* .
4. ADC conversion will become less reliable above maximum frequency.
5. When using ADC hardware averaging, see the *Reference Manual* to determine the most appropriate setting for AVGS.
6. Numbers based on the minimum sampling time of 275 ns.
7. For guidelines and examples of conversion rate calculation, see the *Reference Manual* section 'Calibration function'



R_S	Source Impedance
R_F	Filter Resistance
C_F	Filter Capacitance
R_L	Current Limiter Resistance
R_{SW1}	Channel Selection Switch Impedance
R_{AD}	Sampling Switch Impedance
C_P	Pin Capacitance (two contributions: C_{P1} , C_{P2})
C_S	Sampling Capacitance

Figure 13. ADC input impedance equivalency diagram

6.4.1.2 12-bit ADC electrical characteristics

NOTE

- ADC performance specifications are documented using a single ADC. For parallel/simultaneous operation of both ADCs, either for sampling the same channel by both ADCs or for sampling different channels by each ADC, some amount of decrease in performance can be expected. Care must be taken to stagger the two ADC conversions, in particular the sample phase, to minimize the impact of simultaneous conversions.
- On reduced pin packages where ADC reference pins are shared with supply pins, ADC analog performance characteristics may be impacted. The amount of variation will be directly impacted by the external PCB layout and hence care must be taken with PCB routing. See AN5426 for details

Table 28. 12-bit ADC characteristics (2.7 V to 3 V) (V_{REFH} = V_{DDA}, V_{REFL} = V_{SS})

Symbol	Description	Conditions [1]	Min.	Typ.[2]	Max.	Unit	Notes
V_{DDA}	Supply voltage		2.7	—	3	V	
I_{DDA_ADC}	Supply current per ADC		—	0.6	—	mA	3
SMPLTS	Sample Time		275	—	Refer to the *Reference Manual*	ns	
TUE[4]	Total unadjusted error		—	±4	±8	LSB[5]	6, 7, 8, 9
DNL	Differential non-linearity		—	±1.0	—	LSB[5]	6, 7, 8, 9
INL	Integral non-linearity		—	±2.0	—	LSB[5]	6, 7, 8, 9

1. All accuracy numbers assume the ADC is calibrated with V_{REFH}=V_{DDA}=V_{DD}, with the calibration frequency set to less than or equal to half of the maximum specified ADC clock frequency.
2. Typical values assume V_{DDA} = 3 V, Temp = 25 °C, f_{ADCK} = 40 MHz, R_{AS}=20 Ω, and C_{AS}=10 nF.
3. The ADC supply current depends on the ADC conversion rate.
4. Represents total static error, which includes offset and full scale error.
5. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
6. The specifications are with averaging and in standalone mode only. Performance may degrade depending upon device use case scenario. When using ADC averaging, refer to the *Reference Manual* to determine the most appropriate settings for AVGS.
7. For ADC signals adjacent to V_{DD}/V_{SS} or XTAL/EXTAL or high frequency switching pins, some degradation in the ADC performance may be observed.
8. All values guarantee the performance of the ADC for multiple ADC input channel pins. When using ADC to monitor the internal analog parameters, assume minor degradation.
9. All the parameters in the table are given assuming system clock as the clocking source for ADC.

Table 31. Comparator with 8-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
	Analog comparator hysteresis, Hyst2, Low-speed mode				
	-40 - 125 ℃	—	23	80	
V_{HYST3}	Analog comparator hysteresis, Hyst3, High-speed mode				mV
	-40 - 125 ℃	—	46	200	
	Analog comparator hysteresis, Hyst3, Low-speed mode				
	-40 - 125 ℃	—	32	120	
I_{DAC8b}	8-bit DAC current adder (enabled)				
	3.3V Reference Voltage	—	6	9	μA
	5V Reference Voltage	—	10	16	μA
INL[5]	8-bit DAC integral non-linearity	–0.75	—	0.75	LSB[6]
DNL	8-bit DAC differential non-linearity	–0.5	—	0.5	LSB[6]
t_{DDAC}	Initialization and switching settling time	—	—	30	μs

1. Difference at input > 200mV
2. Applied ± (100 mV + $V_{HYST0/1/2/3}$+ max. of V_{AIO}) around switch point.
3. Applied ± (30 mV + 2 × $V_{HYST0/1/2/3}$+ max. of V_{AIO}) around switch point.
4. Applied ± (100 mV + $V_{HYST0/1/2/3}$).
5. Calculation method used: Linear Regression Least Square Method
6. 1 LSB = $V_{reference}$/256

NOTE

For comparator IN signals adjacent to V_{DD}/V_{SS} or XTAL/EXTAL or switching pins cross coupling may happen and hence hysteresis settings can be used to obtain the desired comparator performance. Additionally, an external capacitor (1nF) should be used to filter noise on input signal. Also, source drive should not be weak (Signal with < 50 K pull up/down is recommended).

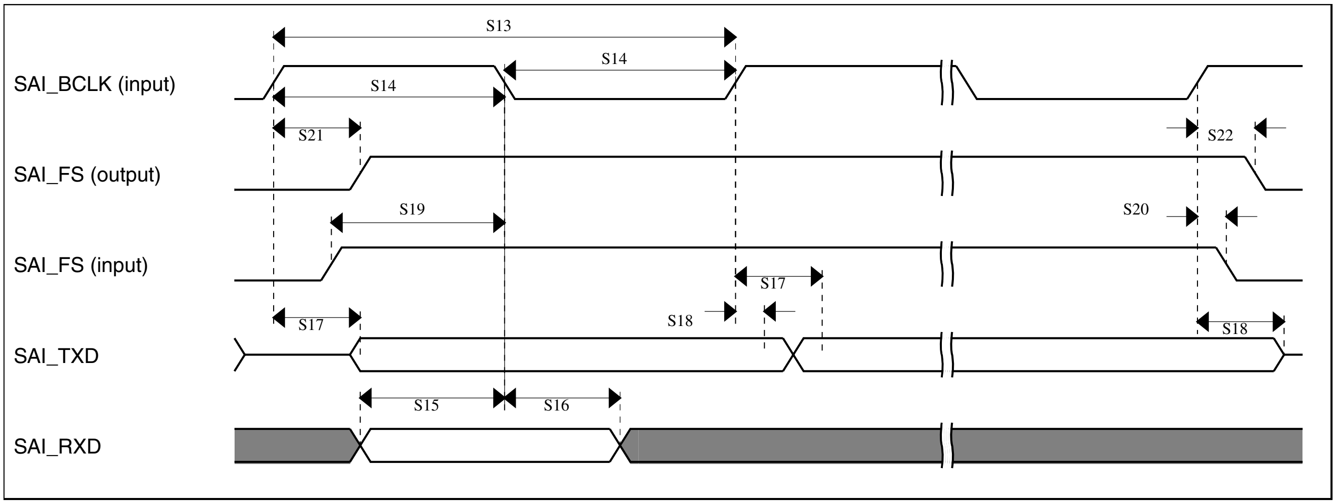


Figure 23. SAI Timing — Slave modes

6.5.6 Ethernet AC specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

The following table describes the MII electrical characteristics.

- Measurements are with maximum output load of 25 pF, input transition of 1 ns and pad configured with fastest slew settings (DSE = 1'b1).
- I/O operating voltage ranges from 2.97 V to 3.6 V
- While doing the mode transition (RUN -> HSRUN or HSRUN -> RUN), the interface should be OFF.

Table 35. MII signal switching specifications

Symbol	Description	Min.	Max.	Unit
—	RXCLK frequency	—	25	MHz
MII1	RXCLK pulse width high	35%	65%	RXCLK period
MII2	RXCLK pulse width low	35%	65%	RXCLK period
MII3	RXD[3:0], RXDV, RXER to RXCLK setup	5	—	ns
MII4	RXCLK to RXD[3:0], RXDV, RXER hold	5	—	ns
—	TXCLK frequency	—	25	MHz
MII5	TXCLK pulse width high	35%	65%	TXCLK period
MII6	TXCLK pulse width low	35%	65%	TXCLK period
MII7	TXCLK to TXD[3:0], TXEN, TXER invalid	2	—	ns
MII8	TXCLK to TXD[3:0], TXEN, TXER valid	—	25	ns

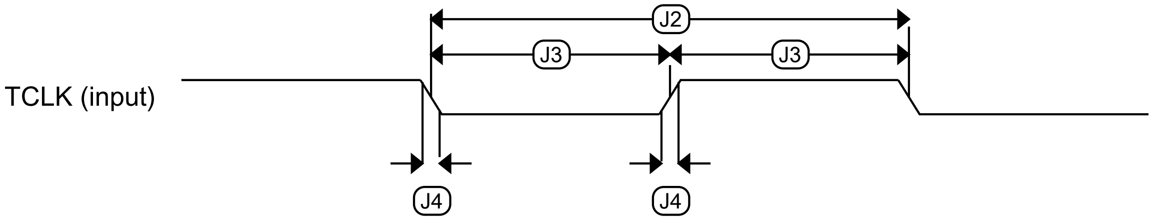


Figure 32. Test clock input timing

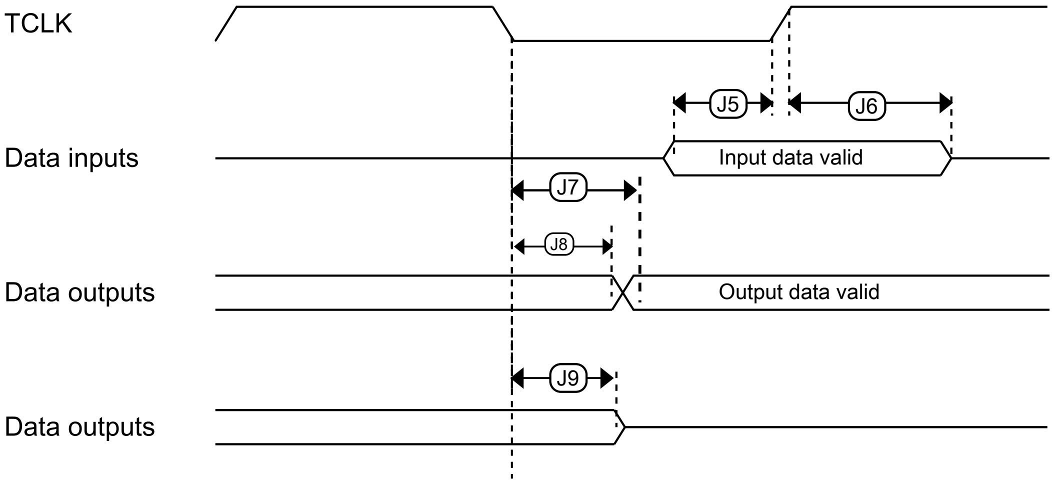


Figure 33. Boundary scan (JTAG) timing

7.3 General notes for specifications at maximum junction temperature

An estimation of the chip junction temperature, T_J, can be obtained from this equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

- T_A = ambient temperature for the package (°C)
- $R_{\theta JA}$ = junction to ambient thermal resistance (°C/W)
- P_D = power dissipation in the package (W)

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. For packages such as the PBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed in the following equation as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

- $R_{\theta JA}$ = junction to ambient thermal resistance (°C/W)
- $R_{\theta JC}$ = junction to case thermal resistance (°C/W)
- $R_{\theta CA}$ = case to ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

Table 43. Revision History (continued)

Rev. No.	Date	Substantial Changes
		- Fixed the typo in R_{SW1} • In LPSPI electrical specifications : - Updated t_{Lead} and t_{Lag} - Added footnote in Figure: LPSPI slave mode timing (CPHA = 0) and Figure: LPSPI slave mode timing (CPHA = 1) • In Thermal characteristics : - Updated the name of table: Thermal characteristics for 32-pin QFN and 48/64/100/144/176-pin LQFP package - Deleted specs for $R_{\theta JC}$ for 32 QFN package - Added '$R_{\theta JCBottom}$'
8	18 June 2018	• In attachement '*S32K1xx_Power_Modes _Configuration*': - Updated VLPR peripherals disabled and Peripherals Enabled use case #1, using 4 Mhz for System clock, 2 Mhz for bus clock, and 1Mhz for flash. • Removed S32K116 from Notes • In figure: S32K1xx product series comparison : - Added note 'Availability of peripherals depends on the pin availability ...' - Updated 'Ambient Operation Temperature' row - Updated 'System RAM (including FlexRAM and MTB)' row for S32K144, S32K146, and S32K148 • In Ordering information : - Updated figure for 'Y: Optional feature' - Updated footnote 3 • In Power and ground pins : - In figure 'Power diagram', updtaed V_{Flash} frequency to 3.3 V • In Power mode transition operating behaviors : - Updated footnote for 'VLPS Mode: All clock sources disabled' • In Power consumption : - Added IDDs for S32K116 - Added VLPR Peripherals enabled use case 2 at 125 °C/Typicals - Renamed VLPR 'Peripherals enabled' to 'Peripherals enabled use case 1' - Added footnote 'Data collected using RAM' to VLPR 'Peripherals disabled' and VLPR 'Peripherals enabled use case 1' - Updated VLPS Peripherals enabled at 25 °C/Typicals for S32K142 and S32K144 to 40 μA and 42 μA respectively - Added table 'VLPS additional use-case power consumption at typical conditions' • In DC electrical specifications at 3.3 V Range : - Updated naming conventions - Added specs for GPIO-FAST pad • In DC electrical specifications at 5.0 V Range : - Updated naming conventions - Added specs for GPIO-FAST pad • In AC electrical specifications at 3.3 V range : - Updated naming conventions - Added specs for GPIO-FAST pad • In AC electrical specifications at 5 V range : - Updated naming conventions - Added specs for GPIO-FAST pad • In External System Oscillator electrical specifications : - Clarified description of g_{mXOSC} - Updated V_{IL} max. to 1.15 V • In Fast internal RC Oscillator (FIRC) electrical specifications :